# **500 MHz Voltage Feedback Op Amp**

NCS2551 is a 500 MHz voltage feedback monolithic operational amplifier featuring high slew rate and low differential gain and phase error. The voltage feedback architecture allows for a superior bandwidth and low power consumption.

#### **Features**

- -3.0 dB Small Signal BW (A<sub>V</sub> = +2.0, V<sub>O</sub> = 0.5 V<sub>p-p</sub>) 500 MHz Typ
- Slew Rate 1400 V/us
- Supply Current 5.5 mA
- Input Referred Voltage Noise 6.0 nV/√Hz
- THD  $-62 \text{ dBc} \text{ (f} = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p})$
- Output Current 100 mA
- Pin Compatible with AD8055, TSH341
- This is a Pb-Free Device

## **Applications**

- Line Drivers
- Radar/Communication Receivers

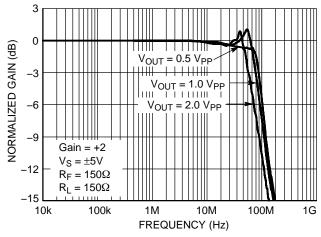


Figure 1. Frequency Response: Gain (dB) vs. Frequency Av = +2.0



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(TSOP-5) **SN SUFFIX CASE 483** 

## **MARKING DIAGRAM**

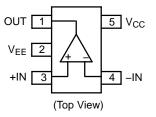


YF1 = Specific Device Code = Assembly Location Α

Υ = Year = Work Week W = Pb-Free Package

(Note: Microdot may be in either location)

## SOT23-5 PINOUT



## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

## PIN FUNCTION DESCRIPTION

Pin (SOT23-5/SC70)	Symbol	Function	Equivalent Circuit
1	OUT	Output	V <sub>CC</sub> ESD OUT V <sub>EE</sub>
2	V <sub>EE</sub>	Negative Power Supply	
3	+IN	Non-inverted Input	V <sub>CC</sub> ESD  IN  V <sub>EE</sub>
4	-IN	Inverted Input	See Above
5	V <sub>CC</sub>	Positive Power Supply	

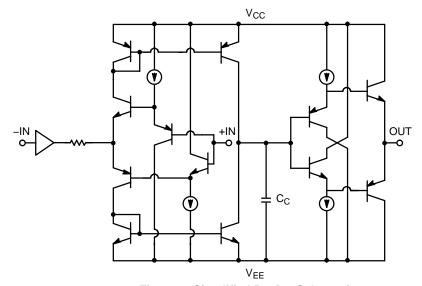


Figure 2. Simplified Device Schematic

## **ATTRIBUTES**

Characte	Value	
ESD Human Body Model Machine Model Charged Device Model		2.0 kV 200 V 1.0 kV
Moisture Sensitivity (Note	Level 1	
Flammability Rating	UL 94 V-0 @ 0.125 in	

<sup>1.</sup> For additional information, see Application Note AND8003/D.

## **MAXIMUM RATINGS**

Parameter	Symbol	Rating	Unit
Power Supply Voltage	V <sub>S</sub>	11	Vdc
Input Voltage Range	V <sub>I</sub>	≤V <sub>S</sub>	Vdc
Input Differential Voltage Range	V <sub>ID</sub>	≤V <sub>S</sub>	Vdc
Output Current	I <sub>O</sub>	100	mA
Maximum Junction Temperature (Note 2)	T <sub>J</sub>	150	°C
Operating Ambient Temperature	T <sub>A</sub>	-40 to +85	°C
Storage Temperature Range	T <sub>stg</sub>	-60 to +150	°C
Power Dissipation	P <sub>D</sub>	(See Graph)	mW
Thermal Resistance, Junction-to-Air	$R_{ hetaJA}$	158	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## **MAXIMUM POWER DISSIPATION**

The maximum power that can be safely dissipated is limited by the associated rise in junction temperature. For the plastic packages, the maximum safe junction temperature is 150°C. If the maximum is exceeded momentarily, proper circuit operation will be restored as soon as the die temperature is reduced. Leaving the device in the "overheated" condition for an extended period can result in device damage.

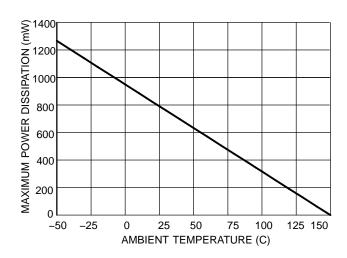


Figure 3. Power Dissipation vs. Temperature

<sup>2.</sup> Power dissipation must be considered to ensure maximum junction temperature (T<sub>J</sub>) is not exceeded.

**AC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +5.0 V,  $V_{EE}$  = -5.0 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUENC	CY DOMAIN PERFORMANCE			•		
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$A_V = +2.0, V_O = 0.5 V_{p-p}$ $A_V = +2.0, V_O = 2.0 V_{p-p}$		500 300		MHz
GF <sub>0.1dB</sub>	0.1 dB Gain Flatness Bandwidth	A <sub>V</sub> = +2.0		15		MHz
dG	Differential Gain	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 \text{ MHz}$		0.06		%
dP	Differential Phase	$A_V = +2.0$ , $R_L = 150 \Omega$ , $f = 3.58 \text{ MHz}$		0.06		٥
TIME DOM	AIN RESPONSE			•		
SR	Slew Rate	$A_V = +2.0, V_{step} = 2.0 V$		1400		V/μs
t <sub>s</sub>	Settling Time 0.1%	A <sub>V</sub> = +2.0, V <sub>step</sub> = 2.0 V		10		ns
t <sub>r</sub> t <sub>f</sub>	Rise and Fall Time	$(10\%-90\%) A_V = +2.0, V_{step} = 2.0 V$		2.4		ns
HARMONIC	NOISE PERFORMANCE					
THD	Total Harmonic Distortion	$f = 5.0 \text{ MHz}, V_{O} = 2.0 V_{p-p}$		-62		dB
HD2	2nd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-68		dBc
HD3	3rd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-63		dBc
IP3	Third-Order Intercept	$f = 10 \text{ MHz}, V_O = 1.0 V_{p-p}$		40		dBm
SFDR	Spurious–Free Dynamic Range	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		63		dBc
e <sub>N</sub>	Input Referred Voltage Noise	f = 1.0 MHz		6.0		nV/√H
i <sub>N</sub>	Input Referred Current Noise	f = 1.0 MHz		3.0		pA/√H

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +5.0 V,  $V_{EE}$  = -5.0 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
DC PERFO	RMANCE		•		•	1
V <sub>IO</sub>	Input Offset Voltage		-10	0	+10	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I <sub>IB</sub>	Input Bias Current	V <sub>O</sub> = 0 V		±3.2	±20	μΑ
$\Delta I_{\text{IB}}/\Delta T$	Input Bias Current Temperature Coefficient	V <sub>O</sub> = 0 V		± 40		nA/°C
NPUT CHA	ARACTERISTICS		_	•	•	•
$V_{CM}$	Input Common Mode Voltage Range (Note 3)		±3.0	± 4.0		V
CMRR	Common Mode Rejection Ratio	(See Graph)	40	50		dB
R <sub>IN</sub>	Input Resistance			4.5		МΩ
C <sub>IN</sub>	Differential Input Capacitance			1.0		pF
OUTPUT C	HARACTERISTICS					
R <sub>OUT</sub>	Output Resistance	Closed Loop Open Loop		0.1 17		Ω
Vo	Output Voltage Range		±3.0	±4.0		V
I <sub>O</sub>	Output Current		±50	±100		mA
POWER SU	JPPLY					
Vs	Operating Voltage Supply			10		V
IS	Power Supply Current		2.0	5.5	10	mA
PSRR	Power Supply Rejection Ratio	(See Graph)	40	60		dB

<sup>3.</sup> Guaranteed by design and/or characterization.

**AC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +2.5 V,  $V_{EE}$  = -2.5 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUEN	CY DOMAIN PERFORMANCE		•		•	
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$A_V = +2.0, V_O = 0.5 V_{p-p}$ $A_V = +2.0, V_O = 1.0 V_{p-p}$		400 200		MHz
GF <sub>0.1dB</sub>	0.1 dB Gain Flatness Bandwidth	A <sub>V</sub> = +2.0		10		MHz
dG	Differential Gain	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.07		%
dP	Differential Phase	$A_V = +2.0$ , $R_L = 150 \Omega$ , $f = 3.58 \text{ MHz}$		0.06		٥
TIME DOM	AIN RESPONSE		•		•	
SR	Slew Rate	$A_V = +2.0, V_{step} = 1.0 V$		800		V/μs
t <sub>s</sub>	Settling Time 0.1%	A <sub>V</sub> = +2.0, V <sub>step</sub> = 1.0 V		10		ns
t <sub>r</sub> t <sub>f</sub>	Rise and Fall Time	$(10\%-90\%) A_V = +2.0, V_{step} = 1.0 V$		2.2		ns
HARMONIC	C/NOISE PERFORMANCE					
THD	Total Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-59		dB
HD2	2nd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-60		dBc
HD3	3rd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-67		dBc
IP3	Third-Order Intercept	$f = 10 \text{ MHz}, V_O = 0.5 V_{p-p}$		35		dBm
SFDR	Spurious–Free Dynamic Range	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		60		dBc
e <sub>N</sub>	Input Referred Voltage Noise	f = 1.0 MHz		6.0		nV/√Hz
i <sub>N</sub>	Input Referred Current Noise	f = 1.0 MHz		3.0		pA/√Hz

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +2.5 V,  $V_{EE}$  = -2.5 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
DC PERFO	RMANCE		_			•
V <sub>IO</sub>	Input Offset Voltage		-10	0	+10	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I <sub>IB</sub>	Input Bias Current	V <sub>O</sub> = 0 V		±3.2	±20	μΑ
$\Delta I_{\text{IB}}/\Delta T$	Input Bias Current Temperature Coefficient	V <sub>O</sub> = 0 V		± 40		nA/°C
NPUT CH	ARACTERISTICS		_			•
$V_{CM}$	Input Common Mode Voltage Range (Note 3)		±0.9	±1.5		V
CMRR	Common Mode Rejection Ratio	(See Graph)	40	50		dB
R <sub>IN</sub>	Input Resistance			4.5		МΩ
C <sub>IN</sub>	Differential Input Capacitance			1.0		pF
OUTPUT C	HARACTERISTICS					
R <sub>OUT</sub>	Output Resistance	Closed Loop Open Loop		0.1 17		Ω
Vo	Output Voltage Range		± 0.9	±1.5		V
Io	Output Current		±50	±100		mA
POWER SI	JPPLY					
Vs	Operating Voltage Supply			5.0	_	V
IS	Power Supply Current		2.0	5.2	10	mA
PSRR	Power Supply Rejection Ratio	(See Graph)	40	60		dB

<sup>4.</sup> Guaranteed by design and/or characterization.

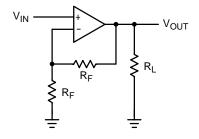


Figure 4. Typical Test Setup (AV = +2.0, RF = 150 kΩ, RL = 150 Ω)

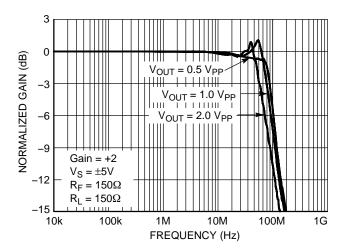


Figure 5. Frequency Response: Gain (dB) vs. Frequency Av = +2.0

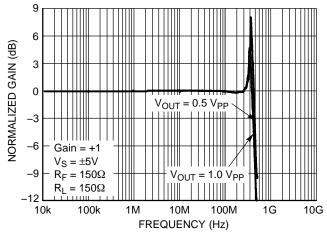


Figure 6. Frequency Response: Gain (dB) vs. Frequency Av = +1.0

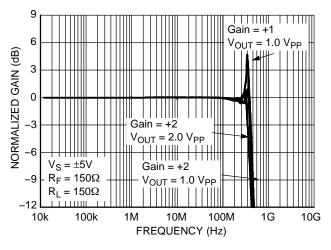


Figure 7. Large Signal Frequency Response Gain (dB) vs. Frequency

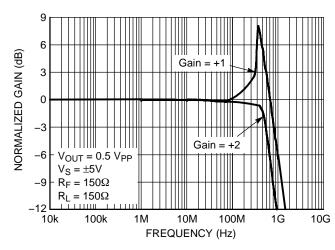


Figure 8. Small Signal Frequency Response Gain (dB) vs. Frequency

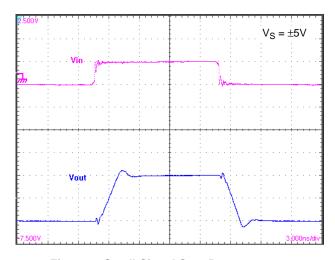


Figure 9. Small Signal Step Response Vertical: 500 mV/div Horizontal: 10 ns/div

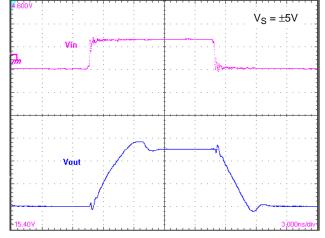


Figure 10. Large Signal Step Response Vertical: 2V/div Horizontal: 10 ns/div

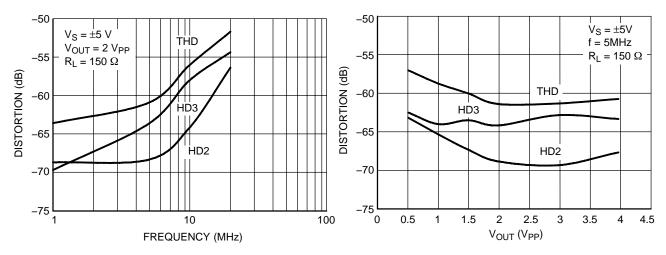


Figure 11. THD, HD2, HD3 vs. Frequency

Figure 12. THD, HD2, HD3 vs. Output Voltage

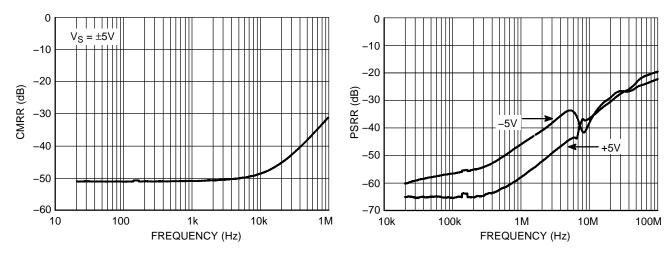


Figure 13. CMRR vs. Frequency

Figure 14. PSRR vs. Frequency

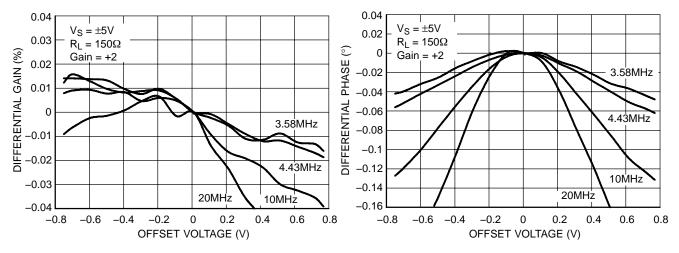


Figure 15. Differential Gain

Figure 16. Differential Phase

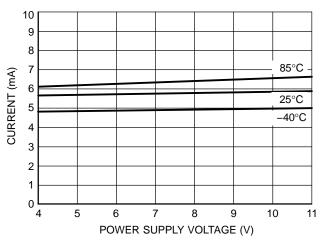
10

9

8

7

6



OUTPUT VOLTAGE (VPP) 5 3

Figure 17. Supply Current vs. Power Supply

Figure 18. Output Voltage Swing vs. Supply Voltage

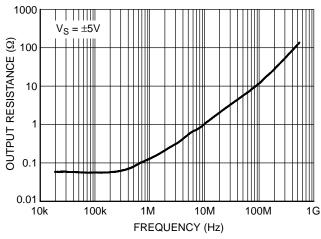
POWER SUPPLY VOLTAGE (V)

85°C

25°C

–40°C

11



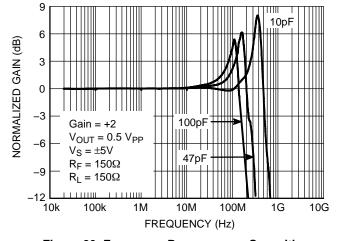


Figure 19. Closed Loop Output Resistance vs. Frequency

Figure 20. Frequency Response vs. Capacitive Load

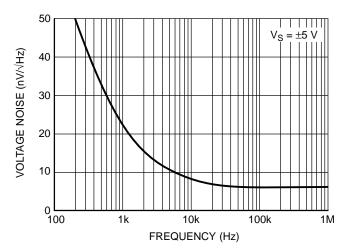


Figure 21. Input Referred Voltage Noise vs. Frequency

## **Printed Circuit Board Layout Techniques**

Proper high speed PCB design rules should be used for all wideband amplifiers as the PCB parasitics can affect the overall performance. Most important are stray capacitances at the output and inverting input nodes as it can effect peaking and bandwidth. A space (3/16" is plenty) should be left around the signal lines to minimize coupling. Also, signal lines connecting the feedback and gain resistors should be short enough so that their associated inductance does not cause high frequency gain errors. Line lengths less than 1/4" are recommended.

## **Video Performance**

This device designed to provide good performance with NTSC, PAL, and HDTV video signals. Best performance is obtained with back terminated loads as performance is degraded as the load is increased. The back termination reduces reflections from the transmission line and effectively masks transmission line and other parasitic capacitances from the amplifier output stage.

#### **ESD Protection**

All device pins have limited ESD protection using internal diodes to power supplies as specified in the attributes table (see Figure 22). These diodes provide moderate protection

to input overdrive voltages above the supplies. The ESD diodes can support high input currents with current limiting series resistors. Keep these resistor values as low as possible since high values degrade both noise performance and frequency response. Under closed—loop operation, the ESD diodes have no effect on circuit performance. However, under certain conditions the ESD diodes will be evident. If the device is driven into a slewing condition, the ESD diodes will clamp large differential voltages until the feedback loop restores closed—loop operation. Also, if the device is powered down and a large input signal is applied, the ESD diodes will conduct.

NOTE: Human Body Model for +IN and -IN pins are rated at 0.8kV while all other pins are rated at 2.0kV.

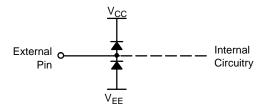


Figure 22. Internal ESD Protection

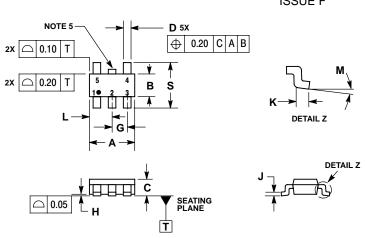
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCS2551SNT1G	SOT23-5 (TSOP-5) (Pb-Free)	3000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## PACKAGE DIMENSIONS

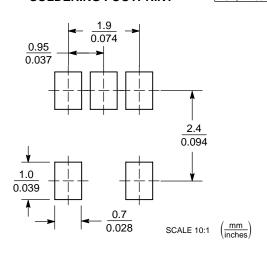
## TSOP-5 CASE 483-02 ISSUE F



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING FER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES
- LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
- OF BASE MATERIAL.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS			
DIM	MIN MAX			
Α	3.00	BSC		
В	1.50	BSC		
С	0.90	1.10		
D	0.25	0.50		
G	0.95	BSC		
Н	0.01	0.10		
J	0.10	0.26		
K	0.20	0.60		
L	1.25	1.55		
М	0° 10°			
S	2.50	3.00		

## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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